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Sheet 1 of 1

INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

Atty.Docket No.: 0756-1139	Serial No. Not Yet Assigned <u>08/355,652</u>
Applicant: Shunpei YAMAZAKI et al.	
Filing Date: December 14, 1994	Group: 1104

U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation
							Yes
							No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

CC	Sameshima et al., "XeCl excimer laser annealing used to fabricate poly-si TFTs, Mat. Res. Soc. Symp. Proc., vol. 71, 1986, pp. 435-440.
CC	Corey et al., "A shallow junction submicrometer PMOS process without high temperature anneals", IEEE electron device letters, vol. 9, no. 10, Oct. 1988, pp. 542-544.
CC	"Fabrication of Submicrometer MOSFET's Using Gas Immersion Laser Doping (GILD) IEEE ELECTRON DEVICE LETTERS Vol. EDL-7, No. 7, pp. 440-442

Examiner	Chandra Chaudhari	Date Considered	7-95
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*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.